ERRATA

MICROCRYSTALLINE SILICON FILMS PREPARED BY VERY HIGH FREQUENCY PLASMA ENHANCED CHEMICAL VAPOR DEPOSITION AT LOW TEMPERATURE

[International Journal of Modern Physics B, Vol. 19, No. 18 (2005) 3013–3020]

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On page 3014, the first sentence of Sec. 3.1 should read as:

Figure 1 shows the deposition rate and photosensitivity of silicon films as a function of the silane concentration at the power density of 0.4 W/cm^2 .

On page 3017, Fig 5 should be shown as follows:

Fig. 5. Raman spectra for films deposited at different power density.

The authors apologize for the errors made.